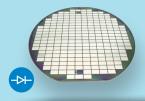


2015 SIPER 12 FEATURED PRODUCTS





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Fast Rectifier Epitaxial Diode





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Hybrid Energy Storage Capacitor

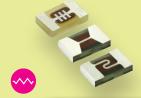
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MEPIC

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SiC620R

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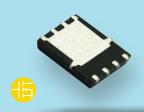


WSHM2818
Current Sense Resistor
7 W Power Rating

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Si7157DP - P-Channel MOSFET Lowest $R_{DS(on)}$, Down to 0.0016 Ω

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PLZ Series - Zener Diodes Very Low Profile, 0.6 mm Typical Height 09



IHLE-4040DC-5A **Power Inductor** E-Field Shielded



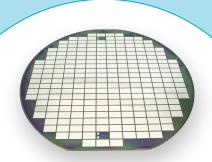
VOW3120 **IGBT** and **MOSFET** Driver Widebody, High-Isolation



AY2 Series Ceramic Safety Capacitors Automotive Grade X1 / Y2

12





FRED Pt® Gen 4 **Diode Chips**

Part of an Ideal Match with Vishay's New Trench IGBT

Features:

- Optimized (600 V / 650 V) to operate in combination with Vishay's new Trench IGBT, available as a kit for easy design
- Offers superior performance, extreme softness, ultra-low V_E (down to 1.4 V) and low $\rm I_{\tiny RRM}$; all the best parameters combined into one product
- Ultra-soft recovery under any switching condition
- Polyimide passivated chip for high reliability
- High operating temperature to +175 °C

- High-frequency converters in power modules, motor drives, UPS, solar inverters, and welding machine inverters
- Single- and three-phase inverters, full- and half-bridge DC/DC converters
- Power factor correction (PFC) circuits, boosters, choppers, and secondary-side rectification



02



196 HVC ENYCAP™

High-Energy Storage Capacitor
Saves Space with the
Industry's Highest Energy
Density (13 Ws/g)



Features:

- Industry-first, polarized energy storage capacitor with high capacitance (up to 90 F) and energy density (13 Ws/g)
- Voltage flexibility: 1.4 V (single cell) to 2.8 V / 4.2 V / 5.6 V / 7.0 V / 8.4 V (multiple cells)
- Available in stacked through-hole (STH, radial), surface-mount flat (SMF) and lay-flat configurations (LFC) with wire and connectors
- Low profile (2.5 mm) to fit portable and compact designs
- Wide variety of layouts

- Power backup for memory controllers, flash backup, RAID systems, SRAM, DRAM
- Power failure and write-cache protection for enterprise SSD and HDD
- Real-time clock power source
- Burst power support for flash lights, wireless transmitters
- Backup power for industrial PCs and industrial controls
- Storage device for energy harvesting
- Emergency lights and micro UPS power sources



03



SiHP33N60EF / EF Series

HV Fast Body Diode Power MOSFET Offers up to 10x Reduction in Q_{rr}

Features:

- Based on E Series Super Junction technology
- ► Fast body diode provides as much as 10x reduction in Q_{rr} over the standard E Series MOSFET for lifetime control
- Designed and developed for soft switching topologies along with similar standard E Series on-resistance values
 - Scales of economy can be achieved within a system using EF series throughout the design (in place of standard E Series MOSFETs with similar on resistance) in the hard switched topology
- ▶ 600 V, 33 A maximum, $R_{DS(on)}$ max of 98 m Ω
- 28 A maximum, R_{DS(on)} max of 123 mΩ option also available (SiHx28N60EF)
- Package options including TO-220, TO-263 (D²PAK), and TO-247AC

- Hard and soft switching (focus) topologies
 - Zero voltage switching (ZVS) and LLC converters
- Applications
 - Renewable energy: PV inverters
 - Industrial: battery chargers
 - Telecom: servers
 - Computing: ATX / silver box SMPS



04



MEPIC

Initiator Resistor with
Predictable, Reproducible
and Reliable Behavior
Meets USCAR and
AKLV16



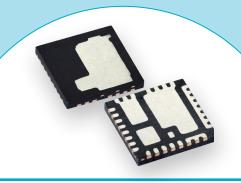
Features:

- Industry-first Massive Electro-Pyrotechnic Initiator Chip resistor
- SMD (0805)
- Ohmic value : 1 Ω to 8 Ω
- Firing energy down to 1.5 mJ
- Firing time down to 250 µs
- Joule effect ignition
- No fire, all fire, ESD, withstands USCAR and AKLV16 standards
- Very predictable, reproducible, and reliable behavior
- Can be adapted for use with various pyrotechnic materials

- Mining electronic detonators (digital blasting)
- Fireworks, electric matches
- Civil detonators for precision blasting



05



SiC620R Integrated Power Stage

Next Generation DrMOS

Features:

- ▶ 20 % lower power losses
- Dual-cooled package enables a 70 A power stage
- ▶ 95 % peak efficiency, over 3 % better efficiency than previous generation
- Optimized package design for up to 1.5 MHz operation
- 50 °C lower operating temperatures for improved reliability
- Zero current detect control for light load efficiency improvement
- Thermally enhanced PowerPAK® MLP55-31L double cooling package
- Low PWM propagation delay (< 20 ns)
- Thermal and undervoltage monitoring

- Servers and workstations
- ► Telecom ASIC power
- Game consoles
- ▶ POL modules
- Graphic cards
- Bitcoin mining hardware



06



WSHM2818

7 W Current Sense Resistor in 2818 Case Size with Resistance Down to 1 mΩ

Features:

- 7 W power rating
- Compact 2818 case size
- Very low resistance values: down to 0.001 Ω
- Low thermal EMF: < 3 μV/°C</p>
- Low inductance: < 5 nH</p>
- Power Metal Strip® technology
- Improved thermal management incorporated into design
- All welded construction
- Low TCR (< 20 ppm/°C)

- Automotive: electronic controls, brushless DC motor controls, battery management
- Industrial: air conditioning / heat pump inverter controls
- Computer: DC/DC converters, VRMs for servers, power management
- Consumer: inverter controls for white goods



07



Si7157DP

Lowest On-Resistance Ever for a P-Channel MOSFET, Down to 0.0016 Ω (max.)



Features:

- ▶ On-resistance at V_{GS} = -10 V: 0.0016 Ω (max.)
- On-resistance at $V_{GS} = -4.5 \text{ V: } 0.002 \Omega \text{ (max.)}$
- Thermally-enhanced PowerPAK® SO-8 package (6.15 mm by 5.15 mm)
- ► Lead (Pb)-free and halogen-free
- ► TrenchFET® Gen III P-Channel Power MOSFET
- ▶ 100 % R_g and UIS tested

- Power management
 - Load switches
 - Battery switches
 - Adapter switches
- Hot-swap applications



08



MMA 0204 HV / MMB 0207 HV

High-Voltage MELF Resistors with 500 V and 1000 V Voltage Ratings



Features:

- Industry-first high-voltage SMD metal film resistor
- High-operating voltage up to 1 kV
- High-surge capability up to 3 kV
- Extremely low voltage coefficient < 0.1 ppm/V</p>
- High accuracy and stability over lifetime
- Matte Sn termination on Ni barrier layer

- Lighting
- Industrial inverters
- Electrical and hybrid vehicles
- Power meters
- High-voltage monitoring of power distribution lines
- Medical power supplies
- Test and measurement equipment



09



PLZ Series

Zener Diodes in Very Low Profile MicroSMF Package with 0.6 mm Typical Height

Features:

- New very low profile surface-mount MicroSMF eSMP® Series package with 0.6 mm typical height
- Power dissipation: 500 mW (despite very small SOD-323 flat lead package style)
- Symmetrical flat leads are double wave (IEC 61760-1) and reflow (JPC/JEDEC J-STD020) solderable for use in automated optical inspection (AOI) systems
- Very tight voltage tolerance: ± 2.5 %
- Designed to withstand ESD pulses
- Excellent stability
- Low leakage current
- RoHS-compliant, halogen-free, and Vishay GREEN

- Switching power supplies
- Electronic lighting
- Computers
- Telecommunications
- Industrial



10



IHLE-4040DC-5A

The Only E-Field Shielded IHLP® Power Inductor



Features:

- Industry-first integrated e-field shield / IHLP
- Reduces e-field up to 20 dB at 1 cm
- Available in 4040 case size
- Eliminates the need for additional Faraday shields
- Available in any standard IHLP value
- Provides a four-terminal contact to the PCB for higher vibration reliability
- AEC-Q200

- DC/DC converter circuits near noise-sensitive components
- Automotive control circuitry
- Engine and transmission control units
- Diesel injection drivers
- Computer and other high-current, noisy power supplies
- Noise suppression for electrical motors
- ► LED drivers
- HID lighting





V0W3120

Widebody High-Isolation and High-Creepage at > 10 mm IGBT and MOSFET Driver

Features:

- ▶ 1414 V working voltage with 2.5 A peak output current enables direct driving of high power IGBTs up to 1200 V / 100 A
- ▶ 8000 V transient voltage and superior common mode rejection (CMR) up to 50 000 V/µs for improved noise isolation
- Integrated undervoltage lock-out function protects IGBTs in case of supply voltage failure
- Wide operating supply voltage range up to 32 V saves voltage regulator
- ▶ 1:1 replacement and industry standard second source

- Industrial:
 - 1 to 3 phase inverters
 - Fixed and variable frequency industrial motor drives
 - Inverter stage in welding equipment
- Alternative energy: voltage converter stage in commercial and residential solar inverters
- Automotive: inverter stage in EV and plug-in HEV chargers



12



AY2 Series

Automotive-Grade X1 / Y2 Ceramic Safety Capacitors

Features:

- Automotive Grade*
- AEC-Q200 qualified
- Can pass 3000 temperature cycles from -55 °C to +125 °C (AEC-Q200 requires 1000)
- X1 / Y2 safety capacitor acc. to IEC 60384-14, 3rd edition
- Widest operating temperature in the market
- Halogen-free epoxy coating

- Automotive
 - On-board chargers in e-cars/PHEVs
 - Battery management in e-cars/PHEVs
 - DC line filtering in DC/DC converters
- Industrial
 - Smart / power meters
 - High-reliability industrial applications and power supplies
 - Automation

^{*} For more information, please visit www.vishay.com/doc?49924

WORLDWIDE SALES CONTACTS



UNITED STATES

VISHAY AMERICAS ONE GREENWICH PLACE SHELTON, CT 06484 **UNITED STATES** PH: +1-402-563-6866

FAX: +1-402-563-6296

SINGAPORE

VISHAY INTERTECHNOLOGY ASIA PTE LTD. 37A TAMPINES STREET 92 #07-00 SINGAPORE 528886 PH: +65-6788-6668 FAX: +65-6788-0988

P.R. CHINA

VISHAY CHINA CO., LTD. 15D, SUN TONG INFOPORT PLAZA 55 HUAI HAI WEST ROAD SHANGHAI 200030 P.R. CHINA

PH: +86-21-22315555 FAX: +86-21-22315551

JAPAN

VISHAY JAPAN CO., LTD. SHIBUYA PRESTIGE BLDG. 4F 3-12-22, SHIBUYA SHIBUYA-KU TOKYO 150-0002 **JAPAN**

PH: +81-3-5466-7150 FAX: +81-3-5466-7160

GERMANY

VISHAY ELECTRONIC GMBH DR.-FELIX-ZANDMAN-PLATZ 1 95100 SELB **GERMANY** PH: +49-9287-71-0

FAX: +49-9287-70435

FRANCE

VISHAY S.A. 199, BD DE LA MADELEINE 06003 NICE, CEDEX 1 **FRANCE**

PH: +33-4-9337-2727 FAX: +33-4-9337-2726

UNITED KINGDOM

VISHAY LTD. SUITE 7A, TOWER HOUSE ST. CATHERINE'S COURT SUNDERLAND ENTERPRISE PARK SUNDERLAND SR5 3XJ **UNITED KINGDOM** PH: +44-191-516-8584 FAX: +44-191-549-9556

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